



100V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
400)/	$23m\Omega$ @ $V_{GS} = 10V$	46.3A
100V	$30m\Omega$ @ $V_{GS} = 6V$	40.5A

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

- Power Management Functions
- DC-DC Converters
- Backlighting

Features

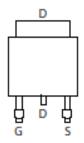
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Q_G Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

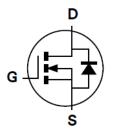
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.33 grams (Approximate)







Pin Out Top View



Equivalent Circuit

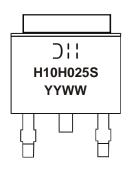
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH10H025SK3-13	TO252 (DPAK)	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



Dill= Manufacturer's Marking
H10H025S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 18 = 2018)
WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	100	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current, V _{GS} = 10V	I _D	46.3 32.7	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	180	Α
Maximum Continuous Body Diode Forward Current (Note 6)	Is	45	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	180	Α	
Avalanche Current, L = 0.1mH (Note 8)		I _{AS}	7.5	Α
Avalanche Energy, L = 0.1mH (Note 8)		E _{AS}	2.8	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P _D	2.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	74	°C/W
Total Power Dissipation (Note 6)		P _D	3.7	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	41	°C/W
Thermal Resistance, Junction to Case		$R_{ heta JC}$	2.0	C/VV
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

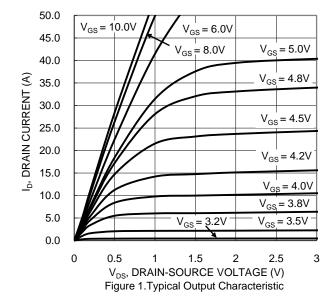
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

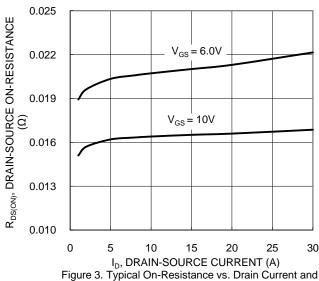
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	1	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	2	_	4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance		_	17.8	23	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Dialit-Source Off-Resistance	R _{DS(ON)}	_	22.9	30	11122	$V_{GS} = 6V, I_D = 20A$	
Diode Forward Voltage	V_{SD}	_	0.9	1.3	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	1544	1			
Output Capacitance	Coss	_	250	l	pF	$V_{DS} = 50V, V_{GS} = 0V, f = 1MHz$	
Reverse Transfer Capacitance	C _{rss}	_	20.4	I			
Gate Resistance	Rg	_	1.26	I	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	21.4	-			
Total Gate Charge (V _{GS} = 6V)	Qg	_	13.4	I	nC	$V_{DD} = 50V, I_D = 20A$	
Gate-Source Charge	Q_{gs}	_	4.6	-	110		
Gate-Drain Charge	Q_{gd}	_	6.0	_			
Turn-On Delay Time	t _{D(ON)}	_	8.2	_		$V_{DD} = 50V, V_{GS} = 10V,$ $I_{D} = 20A, R_{g} = 11\Omega$	
Turn-On Rise Time	t _R	_	11.2	_			
Turn-Off Delay Time	t _{D(OFF)}	_	27.5	_	ns		
Turn-Off Fall Time	t _F	_	13.7	_			
Body Diode Reverse Recovery Time	t _{RR}	_	37.5	_	ns	I 20A di/dt - 100A/ug	
Body Diode Reverse Recovery Charge	Q _{RR}	_	50.9		nC	$I_F = 20A$, di/dt = 100A/ μ s	

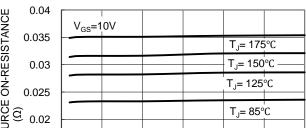
Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.

^{6.} Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.









Gate Voltage

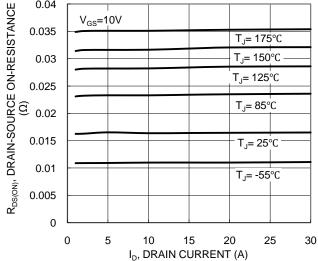
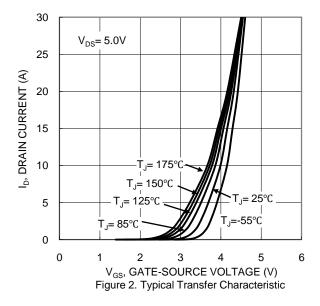
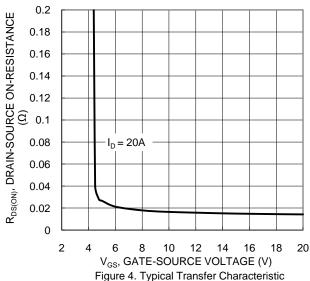


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





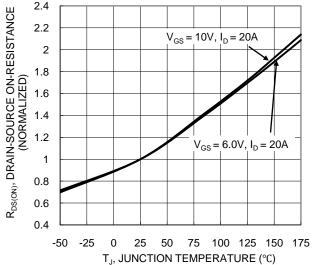
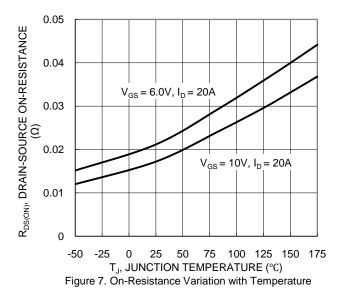
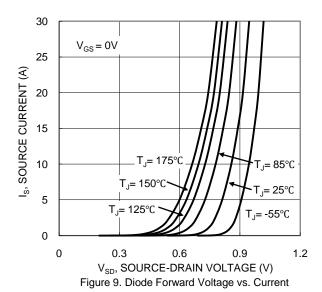


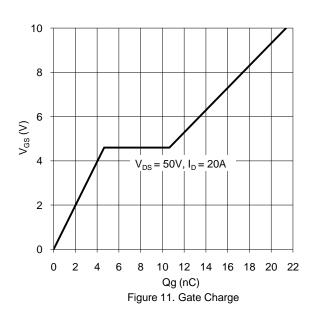
Figure 6. On-Resistance Variation with Temperature

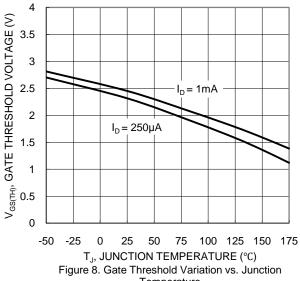




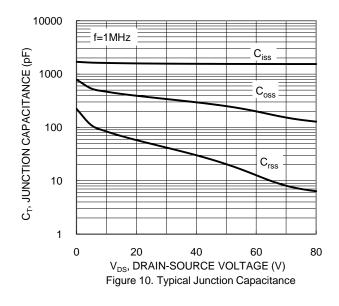


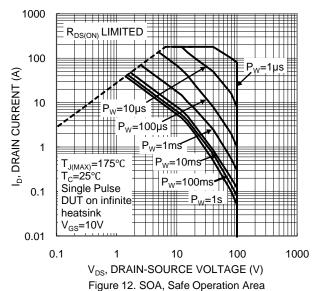




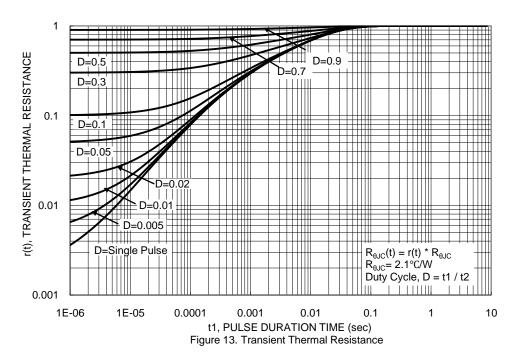


Temperature







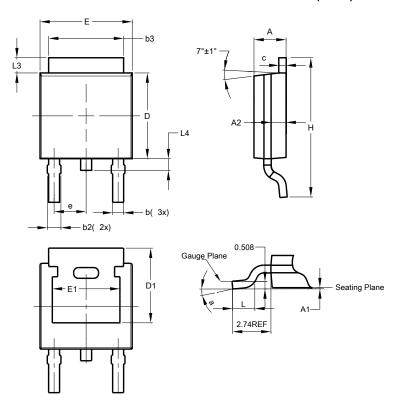




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

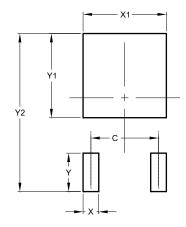


TO252 (DPAK)					
Dim Min		Max	Тур		
Α	2.19	2.39	2.29		
A1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
С	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
Н	9.40	10.41	9.91		
L	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Y	2.600		
Y1	5.700		
Y2	10.700		



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